

SPECIFICATION

参考資料

Device Name : High Voltage Silicon Diode

Type Name : ESJA57-04

1. SCOPE

This specification provide the ratings and the requirements for high voltage silicon diode ESJA57-04 made by FUJI ELECTRIC CO.,LTD.

2. OUT VIEW

Shape and dimensions are described in Fig.

3. IDENTIFICATION

The diode shall be marked with Cathode Mark and Lot No..

4. RATINGS AND CHARACTERISTICS

4.1 ABSOLUTE MAX. RATINGS. (Ta=25 °C unless otherwise noted.)

Items	Conditions	Symbols	Ratings	Units
Repetitive peak reverse voltage.		V_{RRM}	4	kVpeak
Non-Repetitive peak forward current.	50Hz Sine-half wave peak value	I_{FSM}	0.5	Apeak
Average forward current.	50Hz Sine Wave	I_{AV}	5	mA
Allowable junction temperature.		T_j	120	°C
Storage temperature range.		T_{stg}	-40~120	°C
Allowable operating case temperature.		T_c	100	°C

4.2 ELECTRICAL CHARACTERISTICS (Ta=25 °C unless otherwise noted.)

Items	Conditions	Symbols	Ratings	Units
Maximum forward voltage drop	$I_F=10mA$	V_F	15	V
Maximum reverse current	$V_R=4kV$	I_{R1}	2	μA
Maximum reverse current	$V_R=4kV, 100^\circ C$	I_{R2}	5	μA
Maximum reverse recovery time	$I_F=2mA, I_R=4mA$	t_{rr}	0.08	μS
Maximum junction capacitance	$f=1MHz, V_R=0V$	C_j	2	pF

Fuji Electric Co.,Ltd.
Matsumoto Factory

DATE	NAME	APPROVED	Fuji Electric Co.,Ltd.	
DRAWN			DWG.NO.	
CHECKED				

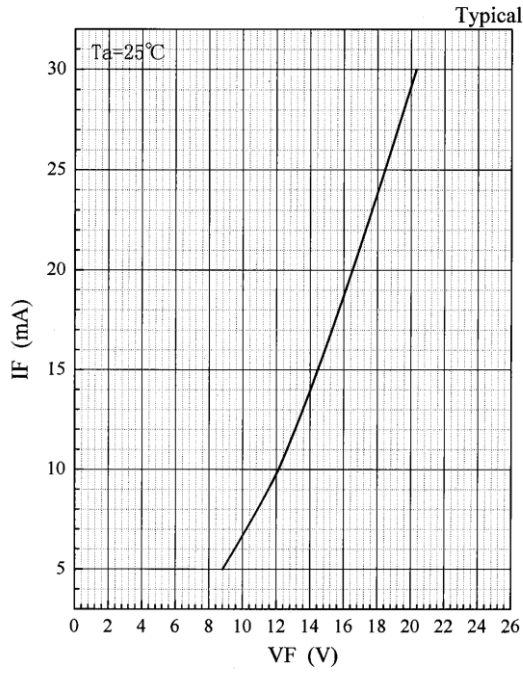


Fig.1 Forward characteristic[VF-IF]

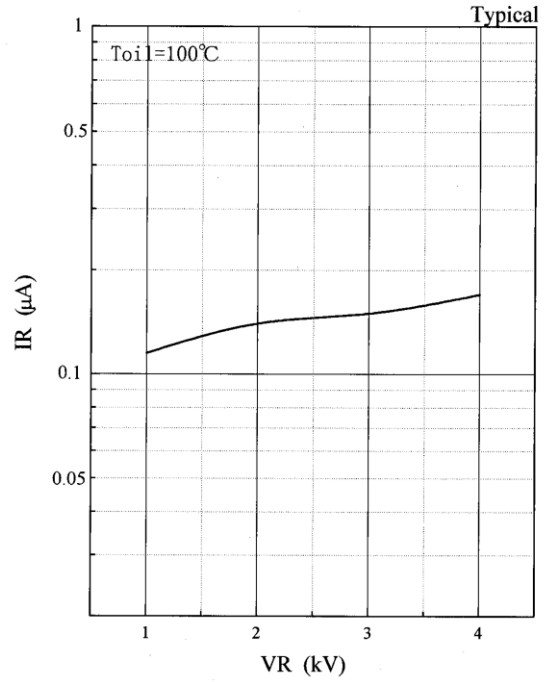


Fig.2 Reverse characteristic[VR-IR]

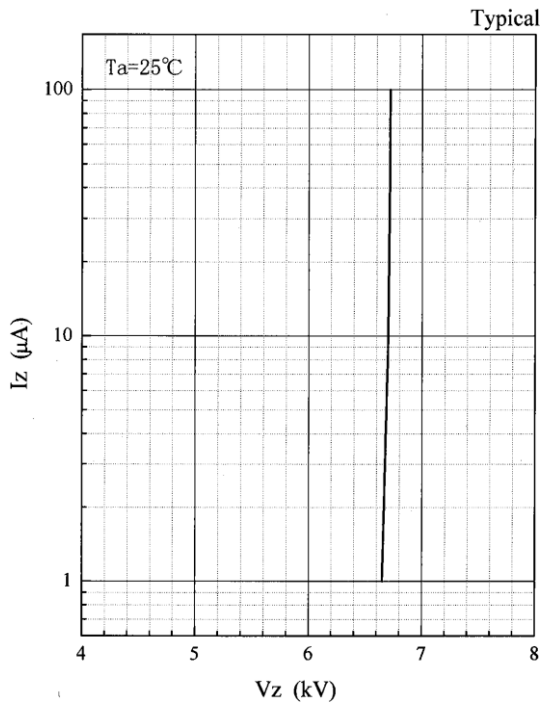


Fig.3 Avalanche characteristic[Vz-Iz]

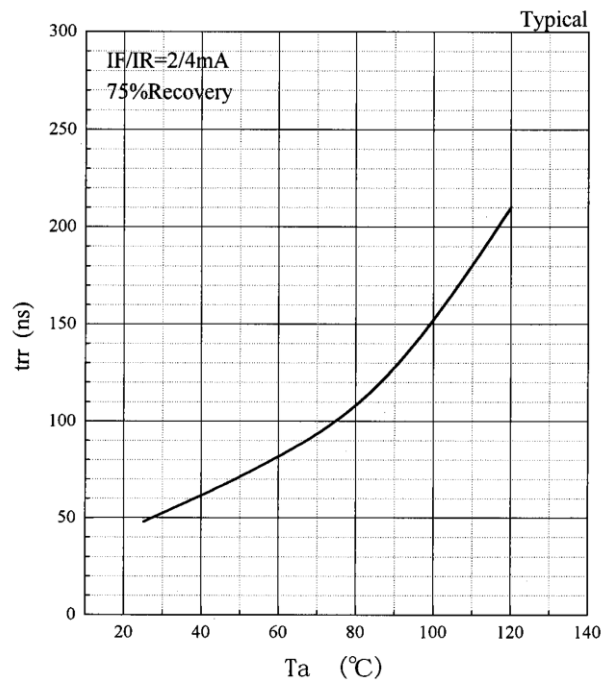


Fig.4 Reverse recovery time characteristic[Ta-trr]

Dimensions

Unit : mm

